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STTH1212

Ultrafast recovery - 1200 V diode

Main product characteristics

I _{F(AV)}	12 A
V _{RRM}	1200 V
Tj	175° C
V _F (typ)	1.25 V
t _{rr} (typ)	50 ns

Features and benefits

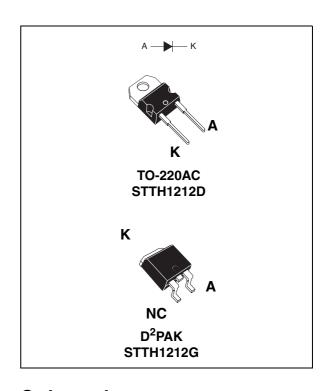
- Ultrafast, soft recovery
- Very low conduction and switching losses
- High frequency and/or high pulsed current operation
- High reverse voltage capability
- High junction temperature

Description

The high quality design of this diode has produced a device with low leakage current, regularly reproducible characteristics and intrinsic ruggedness. These characteristics make it ideal for heavy duty applications that demand long term reliability.

Such demanding applications include industrial power supplies, motor control, and similar mission-critical systems that require rectification and freewheeling. These diodes also fit into auxiliary functions such as snubber, bootstrap, and demagnetization applications.

The improved performance in low leakage current, and therefore thermal runaway guard band, is an immediate competitive advantage for this device.



Order codes

Part Number	Marking
STTH1212D	STTH1212D
STTH1212G	STTH1212G
STTH1212G-TR	STTH1212G

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Characteristics 1

Absolute ratings (limiting values at 25° C, unless otherwise specified) Table 1.

Symbol	Param	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage	Repetitive peak reverse voltage			V
I _{F(RMS)}	RMS forward current	RMS forward current			Α
I _{F(AV)}	Average forward current, $\delta = 0.5$ $T_c = 130^{\circ} C$		12	Α	
I _{FRM}	Repetitive peak forward current $t_p = 5 \mu s$, $F = 5 kHz square$			160	Α
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms Sinusoidal}$			100	Α
T _{stg}	Storage temperature range			-65 to + 175	°C
T _j	Maximum operating junction temperature	9		175	°C

Table 2. Thermal parameter

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case	1.6	°C/W

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _B ⁽¹⁾	Povorce leekage aurrent	T _j = 25° C	V -V			10	
IR'''	Reverse leakage current	T _j = 125° C	$V_R = V_{RRM}$		7	70	μA
		T _j = 25° C				2.2	
$V_F^{(2)}$	Forward voltage drop	T _j = 125° C	I _F = 12 A		1.30	2.0	V
		T _j = 150° C]		1.25	1.9	

^{1.} Pulse test: t_p = 5 ms, δ < 2 %

To evaluate the conduction losses use the following equation: P = 1.5 x $I_{F(AV)}$ + 0.033 $I_{F}^{2}_{(RMS)}$

$$P = 1.5 \times I_{F(AV)} + 0.033 I_{F^{2}(RMS)}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2 %

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Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Тур	Max.	Unit
+		$I_F = 1 \text{ A, } dI_F/dt = -50 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$			100	ns
t _{rr}	Reverse recovery time	$I_F = 1 \text{ A, } dI_F/dt = -100 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$		50	70	115
I _{RM}	Reverse recovery current	$I_F = 12 \text{ A}, dI_F/dt = -200 \text{ A/}\mu\text{s}, \ V_R = 600 \text{ V}, T_j = 125^{\circ} \text{ C}$		16	24	Α
S	Softness factor	$I_F = 12 \text{ A}, dI_F/dt = -200 \text{ A/}\mu\text{s}, \ V_R = 600 \text{ V}, T_j = 125^{\circ} \text{ C}$		2		
t _{fr}	Forward recovery time	$I_F = 12 \text{ A}$ $dI_F/dt = 50 \text{ A/}\mu\text{s}$ $V_{FR} = 1.5 \text{ x } V_{Fmax}, T_j = 25^{\circ} \text{ C}$			400	ns
V _{FP}	Forward recovery voltage	$I_F = 12 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A/}\mu\text{s},$ $T_j = 25^{\circ} \text{ C}$		6		٧

Figure 1. Conduction losses versus average current

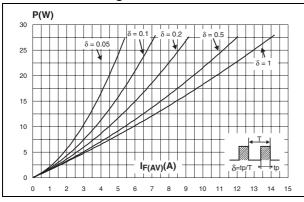
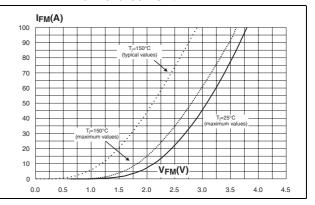


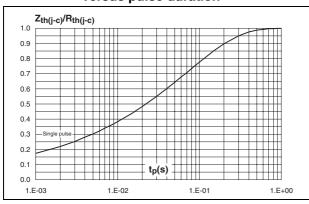
Figure 2. Forward voltage drop versus forward current



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Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (typical values)



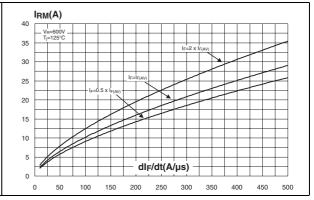
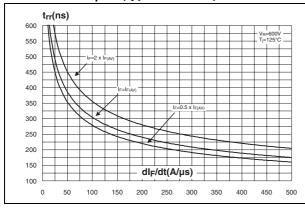


Figure 5. Reverse recovery time versus dl_F/dt (typical values)

Figure 6. Reverse recovery charges versus dl_F/dt (typical values)



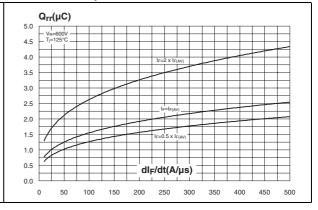
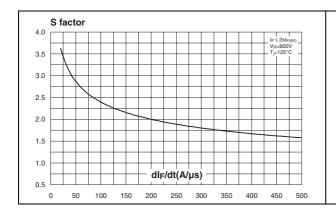
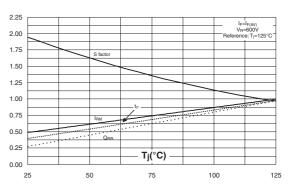


Figure 7. Softness factor versus dl_F/dt (typical values)

Figure 8. Relative variations of dynamic parameters versus junction temperature



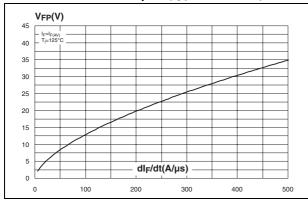


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Figure 9. Transient peak forward voltage versus dl_F/dt (typical values)

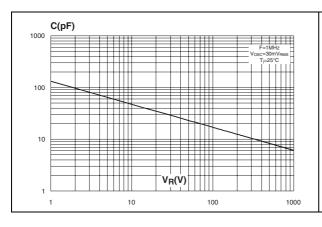
Figure 10. Forward recovery time versus dl_F/dt (typical values)

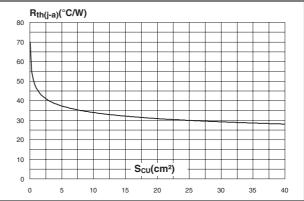


t_{fr}(ns) dlf/dt(A/µs)

Figure 11. Junction capacitance versus reverse voltage applied (typical values)

Figure 12. Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, e_{cu} = 35 μ m)





2 Package mechanical data

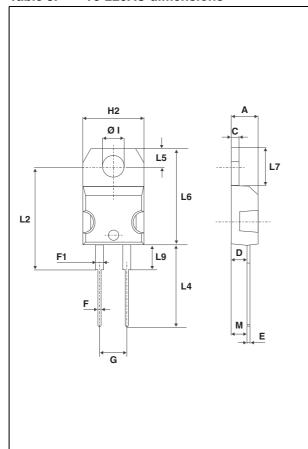
Epoxy meets UL94, V0

Cooling method: by conduction (C)

Recommended torque value: 0.55 Nm (TO-220AC)

Maximum torque value: 0.7 Nm (TO-220AC)

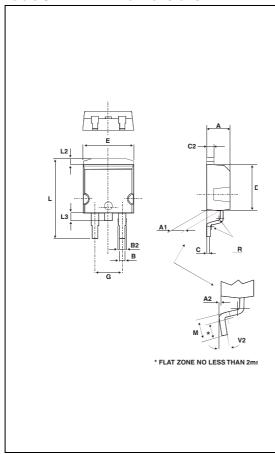
Table 5. T0-220AC dimensions



		DIMEN	SIONS	
REF.	Millimeters		Inc	hes
	Min.	Max.	Min.	Max.
Α	4.40	4.60	0.173	0.181
С	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
Е	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.00 10.40		0.409
L2	16.40	O typ.	0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
М	2.6 typ.		0.102	2 typ.
Diam. I	3.75	3.85	0.147	0.151

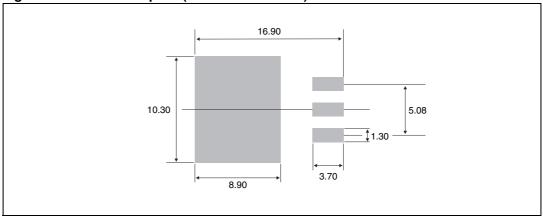
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Table 6. D²PAK dimensions



		DIMEN	ISIONS		
REF.	Millim	neters	Inc	hes	
	Min.	Max	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
A1	2.49	2.69	0.098	0.106	
A2	0.03	0.23	0.001	0.009	
В	0.70	0.93	0.027	0.037	
B2	1.14	1.70	0.045	0.067	
С	0.45	0.60	0.017	0.024	
C2	1.23	1.36	0.048	0.054	
D	8.95	9.35	0.352	0.368	
Е	10.00	10.40	0.393	0.409	
G	4.88	5.28	0.192	0.208	
L	15.00	15.85	0.590	0.624	
L2	1.27	1.40	0.050	0.055	
L3	1.40	1.75	0.055	0.069	
М	2.40	3.20	0.094	0.126	
R	0.40 typ.		0.010	6 typ.	
V2	0°	8°	0°	8°	

Figure 13. D²PAK footprint (dimensions in mm)



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

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Ordering information STTH1212

3 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH1212D	STTH1212D	TO-220AC	1.86 g	50	Tube
STTH1212G	STTH1212G	D ² PAK	1.48 g	50	Tube
STTH1212G-TR	STTH1212G	D ² PAK	1.48 g	1000	Tape & reel

4 Revision history

Date	Revision	Description of Changes
02-Mar-2006	1	First issue.

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